

μ PA2735GR

P-channel MOSFET

 $-30 \text{ V}, -16 \text{ A}, 5.0 \text{ m}\Omega$

R07DS1319EJ0100 Rev.1.00 Jan 25, 2016

Description

The μ PA2735GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- $V_{DSS} = -30 \text{ V } (T_A = 25^{\circ}\text{C})$
- Low on-state resistance
 - --- R_{DS(on)} = 5.0 mΩ MAX. (V_{GS} = -10 V, I_D = -16 A)
- 4.5 V Gate-drive available
- Small and surface mount package (SOP-8)
- Pb-free and Halogen free



Power SOP8

Ordering Information

Part No.	LEAD PLATING	PACKING	Package	
μ PA2735GR-E1-AX	Ni / Pd / Au	Tape 2500 p/reel	SOP-8	
μ PA2735GR-E2-AX	NI / Pu / Au		0.085 g TYP.	

Absolute Maximum Ratings ($T_A = 25$ °C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V_{DSS}	-30	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	∓20	V
Drain Current (DC)	I _{D(DC)}	∓16	А
Drain Current (pulse) *1	I _{D(pulse)}	∓150	Α
Total Power Dissipation *2	P _{T1}	1.1	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	2.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current *3	I _{AS}	16	Α
Single Avalanche Energy *3	E _{AS}	25.6	mJ

Thermal Resistance

Channel to Ambient Thermal Resistance *2 R_{th(ch-A)} 114 °C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

*3. Starting T_{ch} = 25°C, V_{DD} = -15 V, R_G = 25 Ω , V_{GS} = -20 \rightarrow 0 V, L = 100 μH

Electrical Characteristics (T_A = 25°C)

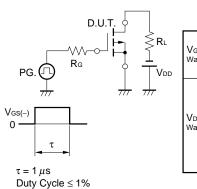
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			∓100	nA	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	-1.0		-2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	10			S	$V_{DS} = -10 \text{ V}, I_{D} = -8.0 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		3.8	5.0	mΩ	$V_{GS} = -10 \text{ V}, I_D = -16 \text{ A}$
Resistance *1	R _{DS(on)2}		5.1	7.8	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -16 \text{ A}$
Input Capacitance	C _{iss}		6250		pF	$V_{DS} = -10 \text{ V},$
Output Capacitance	Coss		3900		pF	$V_{GS} = 0 V$,
Reverse Transfer Capacitance	C _{rss}		2850		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		35		ns	$V_{DD} = -15 \text{ V}, I_D = -8.0 \text{ A},$
Rise Time	t _r		85		ns	$V_{GS} = -10 \text{ V},$
Turn-off Delay Time	$t_{d(off)}$		300		ns	$R_G = 10 \Omega$
Fall Time	t _f		400		ns	
Total Gate Charge	Q_{G}		195		nC	$V_{DD} = -24 \text{ V},$
Gate to Source Charge	Q _{GS}		15		nC	$V_{GS} = -10 \text{ V},$
Gate to Drain Charge	Q_{GD}		100		nC	$I_D = -16 \text{ A}$
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.82		V	$I_F = 16 \text{ A}, V_{GS} = 0 \text{ V}$
Reverse Recovery Time	t _{rr}		60		ns	$I_F = 16 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q _{rr}		88		nC	di/dt = 100 A/μs

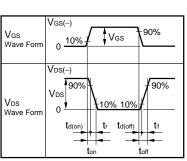
Note: *1. Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

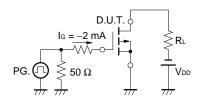
$PG. \square \qquad PG. \square \qquad PG.$

TEST CIRCUIT 2 SWITCHING TIME





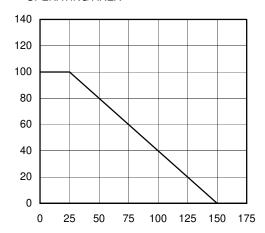
TEST CIRCUIT 3 GATE CHARGE



dT - Percentage of Rated Power - %

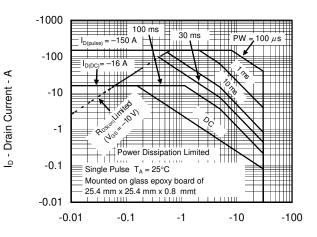
TYPICAL CHARACTERISTICS (T_A = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



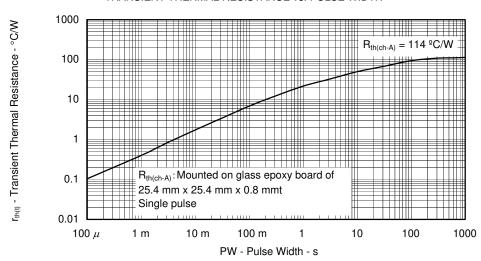
T_A - Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA

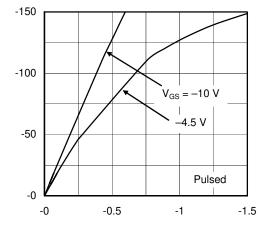


V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

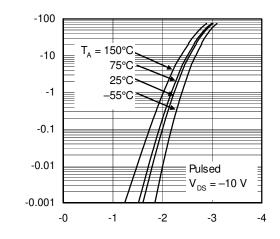


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS



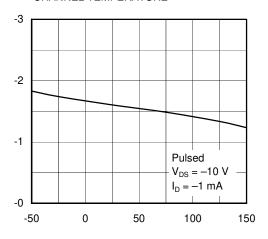
V_{GS} - Gate to Source Voltage - V

I_D - Drain Current - A

lo - Drain Current - A

 $V_{\text{GS}(\text{off})}$ – Gate to Source Cut-off Voltage - V

GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



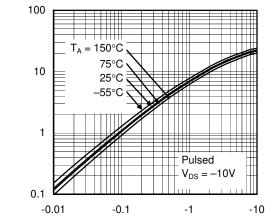
T_{ch} - Channel Temperature - °C

$y_{\rm ls}$ | - Forward Transfer Admittance - S

R_{DS(on)} - Drain to Source On-state Resistance - mΩ

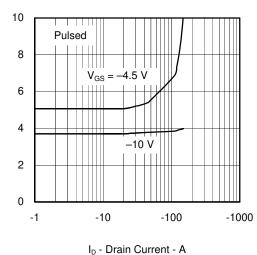
Ciss, Coss, Crss - Capacitance - pF

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

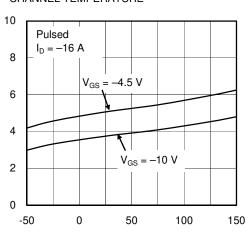


I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

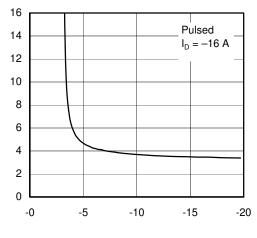


DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



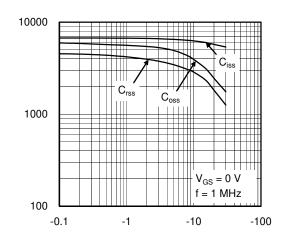
T_{ch} - Channel Temperature - °C

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

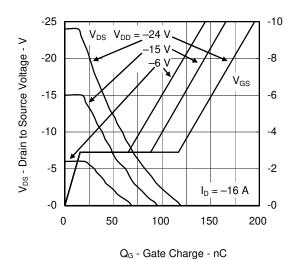
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



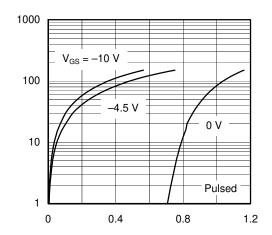
V_{DS} - Drain to Source Voltage - V

 $R_{DS(on)}$ - Drain to Source On-state Resistance - $m\Omega$

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



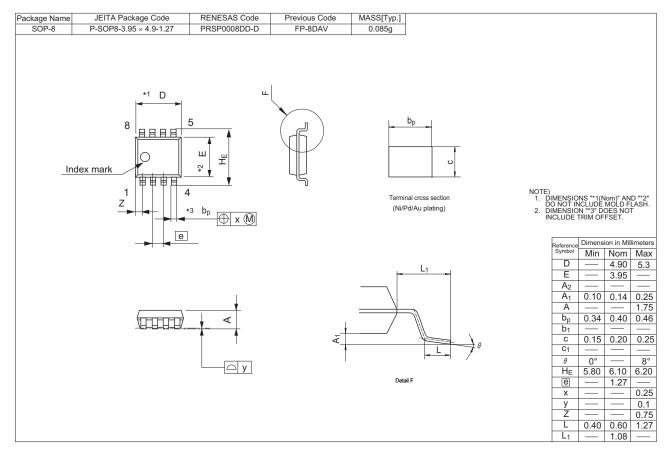
 $V_{\text{F(S-D)}}$ - Source to Drain Voltage - V

 $\ensuremath{\mathsf{V}}_{\ensuremath{\mathsf{GS}}}$ - Gate to Source Voltage - V

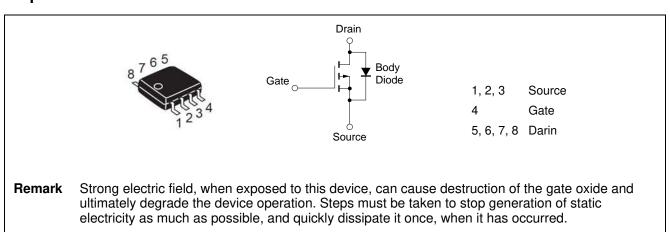
I_F - Diode Forward Current - A

Package Drawings (Unit: mm)

SOP-8



Equivalent Circuit



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